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With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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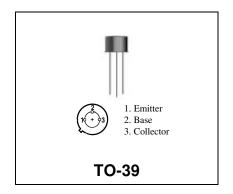
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**MRF545** 

# RF & MICROWAVE DISCRETE LOW POWER TRANSISTORS

#### **Features**

- Silicon PNP, high Frequency, high breakdown Transistor
- Maximum Unilateral Gain = 14 dB (typ) @ f = 200 MHz
- High Collector Base Breakdown Voltage BVCBO = 100 V (min)
- High F<sub>T</sub> 1400 MHz



#### DESCRIPTION:

Designed primarily for use in high frequency and medium and high resolution color video display monitors as well as other applications requiring high breakdown characteristics.

### ABSOLUTEMAXIMUM RATINGS (Tcase = 25°C)

Symbol	Parameter	Value	Unit
V <sub>CEO</sub>	Collector-Emitter Voltage	70	Vdc
V <sub>CBO</sub>	Collector-Base Voltage	100	Vdc
V <sub>EBO</sub>	Emitter-Base Voltage	3.0	Vdc
I <sub>C</sub>	Collector Current	400	mA

#### Thermal Data

PD	Total Device Dissipation @ T <sub>A</sub> = 25° C	3.5	Watts
	Derate above 25° C	20	mW/ º <b>C</b>
Tstg	Storage Temperature Range	-65 to +200	ο̄C



### **MRF545**

### ELECTRICAL SPECIFICATIONS (Tcase = 25°C)

### **STATIC**

(off)

0	Total Constitutions		Value			
Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
BVCEO	Collector-Emitter Breakdown Voltage (IC = 1.0 mAdc, IB = 0)	70	-	-	Vdc	
BVCBO	Collector-Base Breakdown Voltage (IC= 100 μAdc, IE=0)	100	-	-	Vdc	
BVEBO	Emitter-Base Breakdown Voltage (IE = 100 μAdc, IC = 0)	3.0	-	-	Vdc	
ICBO	Collector Cutoff Current (VCE = 80 Vdc, IE = 0 Vdc)	-	-	20	μΑ	
ICES	Collector Cutoff Current (VCE = 80 Vdc, IE = 0 Vdc)	-	1.0	100	μΑ	

(on)

 (011)					
HFE	DC Current Gain (IC = 50 mAdc, VCE = 6.0 Vdc)	15	-	-	

### **DYNAMIC**

Symbol	Test Conditions		Unit		
	rest Conditions	Min.	Тур.	Max.	Oilit
СОВ	Output Capacitance (VCB = 10Vdc, IE=0, f=1 MHz)	-	2.5	-	pF
CIB	Input Capacitance (VEB = 3Vdc, IE=0, f=1 MHz)	-	5.4	-	pF
ССВ	Junction Capacitance (VCB = 10Vdc, IE=0, f=1 MHz)	-	2.8	3.2	pF
f <sub>T</sub>	Current-Gain - Bandwidth Product (IC = 50 mAdc, VCE = 25 Vdc, f = 250 MHz)	1000	1400	-	MHz



### **MRF545**

### **FUNCTIONAL**

0	Total Complisions			Value		
Symbol	rest C	Test Conditions		Тур.	Max.	Unit
G <sub>U max</sub>	Maximum Unilateral Gain	IC = 50 mAdc, VCE = 25Vdc, f = 200 MHz	-	14	-	dB
MAG	Maximum Available Gain	IC = 50 mAdc, VCE = 25Vdc, f = 200 MHz	-	14.5	-	dB
S <sub>21</sub>   <sup>2</sup>	Insertion Gain	IC = 50 mAdc, VCE = 25Vdc, f = 200 MHz	11.5	12.5	-	dB

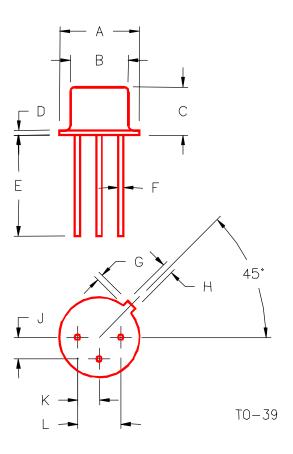
Table 1. Common Emitter S-Parameters, @ VCE = 25 V, IC = 50 mA

f	Si	11	S	)1	S	12	g	322
(MHz)	S11	∠ ф	S21	∠ φ	S12	∠ ф	S22	∠ φ
100	0.139	-105	7.43	101	0.031	83	0.573	-19
200	0.162	-168	4.35	80	0.066	82	0.508	-23
300	0.522	130	1.7	75	0.113	85	0.493	-29
400	0.260	129	2.23	63	0.154	85	0.487	-43
500	0.275	133	1.74	54	0.188	71	0.445	-53
600	0.262	123	1.49	46	0.226	74	0.495	-69
700	0.333	118	0.951	45	0.925	75	0.456	-71
800	0.327	122	1.3	35	0.379	66	0.424	-85
900	0.517	97	1.21	30	0.402	61	0.393	-109
1000	0.463	115	1.07	27	0.437	63	0.375	-115









	MINIMUM	MAXIMUM		MINIMUM	MAXIMUM
	INCHES/MM	INCHES/MM		INCHES/MM	INCHES/MM
Α	.350/8,89	.370/9,40	J	.095/2,41	.105/2,67
В	.315/8,00	.335/8,51	K	.095/2,41	.105/2,67
С	.240/6,10	.260/6,60	L	.190/4,83	.210/5,33
D	.015/0,38	.045/1,14			
Ε	.500/	12,70			
F	.016/0,41	.019/0,48			
G	.029/0,74	.040/1,02			
Н	.028/0,71	.034/0,86			